



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



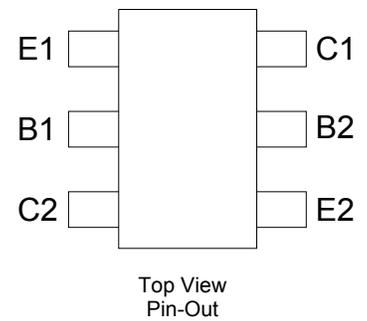
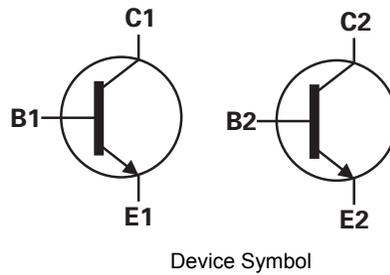
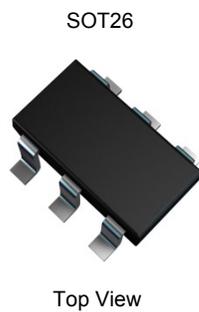
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Features

- $BV_{CE0} > 60V$
- $I_C = 1A$ high Continuous Collector Current
- $I_{CM} = 2A$ Peak Pulse Current
- $R_{CE(sat)} = 100m\Omega$ for a Low Equivalent On-Resistance
- Low Saturation Voltage $V_{CE(sat)} < 250mV @ 1A$

Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 [Ⓔ]
- Weight: 0.015 grams (approximate)



Absolute Maximum Ratings – Q1 & Q2 Common (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	5	V
Continuous Collector Current	I _C	1	A
Peak Pulse Collector Current	I _{CM}	2	A
Base current	I _B	300	mA
Peak Pulse Base current	I _{BM}	1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

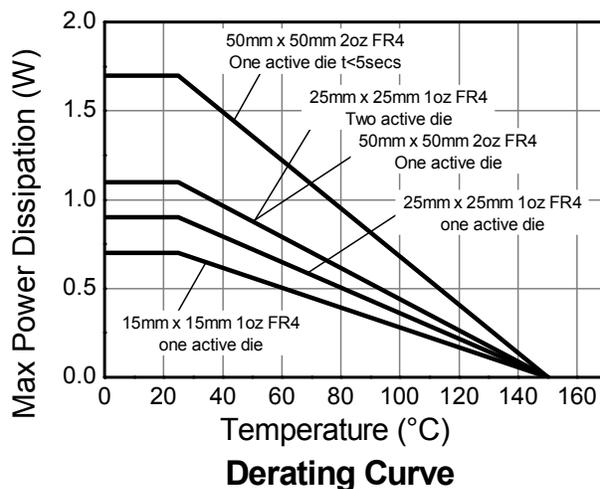
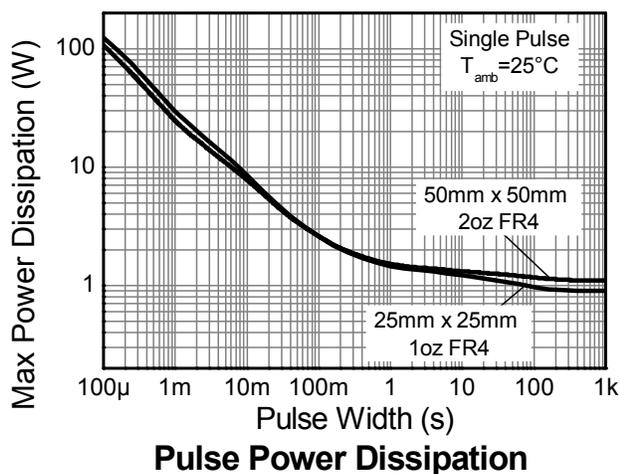
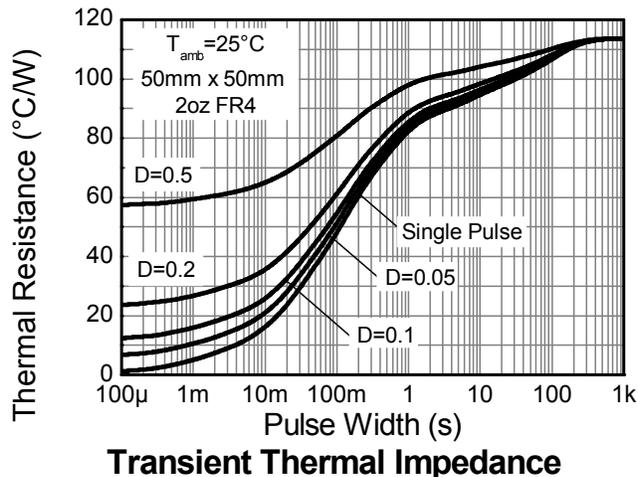
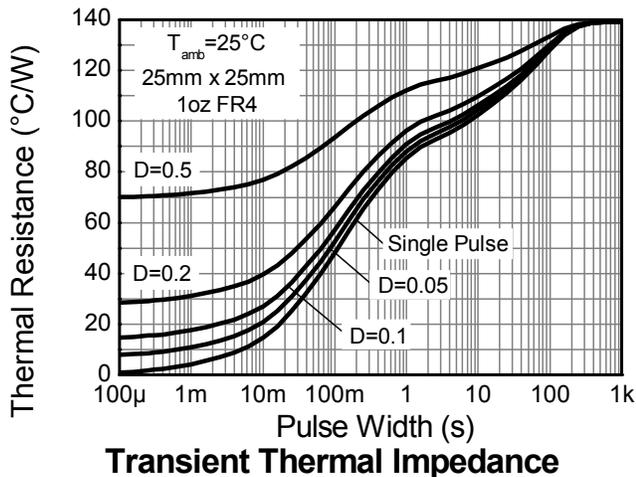
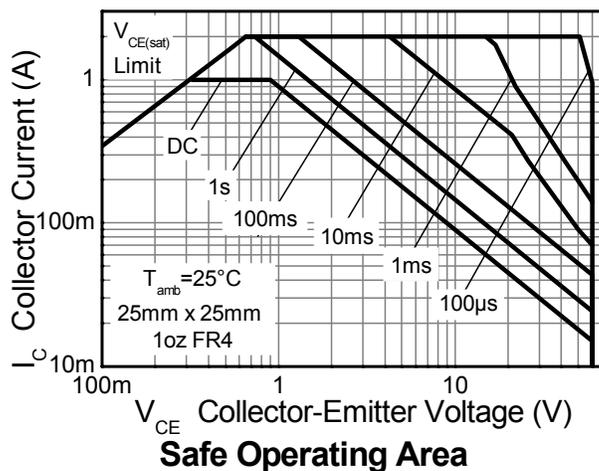
Characteristic	Symbol	Value	Unit	
Power Dissipation Linear Derating Factor	P _D	0.7	W mW/°C	
		(Notes 5 & 9)		5.6
		(Notes 6 & 9)		0.9
				7.2
		(Notes 6 & 10)		1.1
				8.8
Thermal Resistance, Junction to Ambient	R _{θJA}	1.1	°C/W	
		(Notes 5 & 9)		8.8
		(Notes 6 & 9)		1.7
		(Notes 6 & 10)		13.6
		(Notes 7 & 9)		179
Thermal Resistance, Junction to Lead	R _{θJL}	96	°C/W	
		(Notes 8 & 9)		139
		(Notes 6 & 9)		113
		(Notes 6 & 10)		113
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 12)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
 7. Same as note (5), except the device is mounted on 50mm x 50mm 2oz copper.
 8. Same as note (7), except the device is measured at t < 5 seconds.
 9. One active die operating with the collector attached to the heatsink.
 10. Two active dice running at equal power with heatsink split 50% to each collector.
 11. Thermal resistance from junction to solder-point (at the end of the collector lead).
 12. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information



Electrical Characteristics - Q1 & Q2 common (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	80	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 13)	BV _{CEO}	60	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	5	—	—	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	—	—	100	nA	V _{CB} = 60V, I _E = 0A
		—	—	50	μA	V _{CB} = 60V, I _E = 0A, T _J = +150°C
Collector-Emitter Cutoff Current	I _{CES}	—	—	100	nA	V _{CES} = 60V, V _{BE} = 0V
Emitter-Base Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = 5V, I _C = 0A
DC Current Gain (Note 13)	h _{FE}	250	380	—	—	I _C = 1mA, V _{CE} = 5V
		200	420	—		I _C = 500mA, V _{CE} = 5V
		100	380	—		I _C = 1A, V _{CE} = 5V
Collector-Emitter Saturation Voltage (Note 13)	V _{CE(sat)}	—	60	110	mV	I _C = 100mA, I _B = 1mA
		—	70	140		I _C = 500mA, I _B = 50mA
		—	100	250		I _C = 1A, I _B = 100mA
Equivalent On-Resistance	R _{CE(sat)}	—	100	250	mΩ	I _C = 1A, I _B = 100mA
Base-Emitter Saturation Voltage (Note 13)	V _{BE(sat)}	—	940	1100	mV	I _C = 1A, I _B = 50mA
Base-Emitter Turn-On Voltage (Note 13)	V _{BE(on)}	—	780	900	mV	I _C = 1A, V _{CE} = 5V
Output Capacitance	C _{obo}	—	5.5	10	pF	V _{CB} = 10V, f = 1MHz
Transition Frequency	f _T	150	220	—	MHz	V _{CE} = 10V, I _C = 50mA f = 100MHz
Turn-On Time	t _{on}	—	63	—	ns	V _{CC} = 10V, I _C = 0.5A I _{B1} = -I _{B2} = 25mA
Delay Time	t _d	—	33	—	ns	
Rise Time	t _r	—	30	—	ns	
Turn-Off Time	t _{off}	—	420	—	ns	
Storage Time	t _s	—	380	—	ns	
Fall Time	t _f	—	40	—	ns	

Notes: 13. Measured under pulsed conditions. Pulse width ≤ 300 μs. Duty cycle ≤ 2%

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

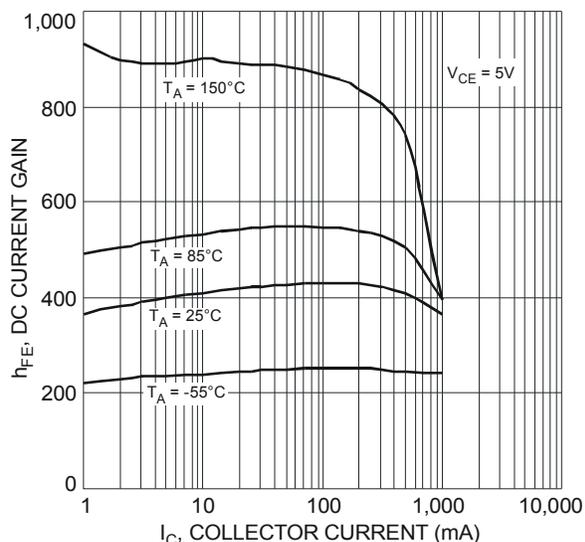


Fig. 5 Typical DC Current Gain vs. Collector Current

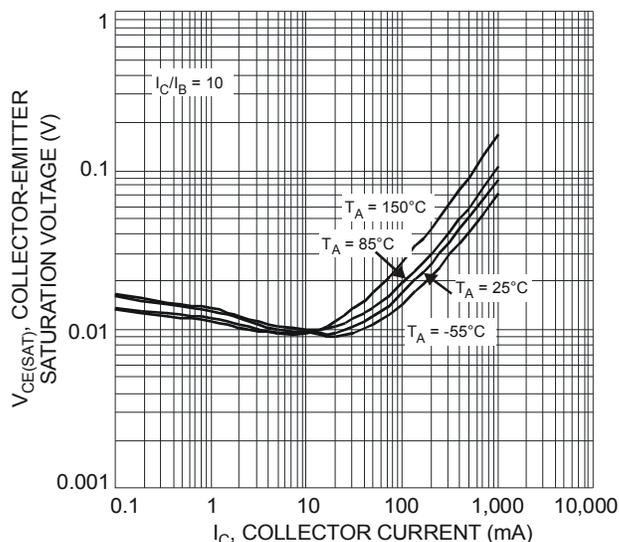


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

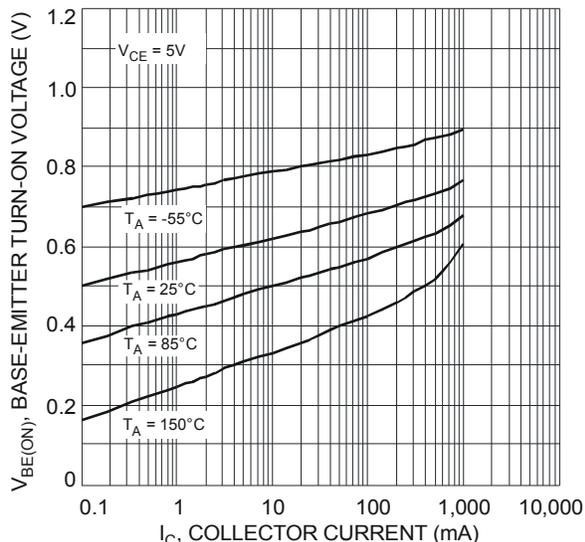


Fig. 7 Typical Base-Emitter Turn-On Voltage vs. Collector Current

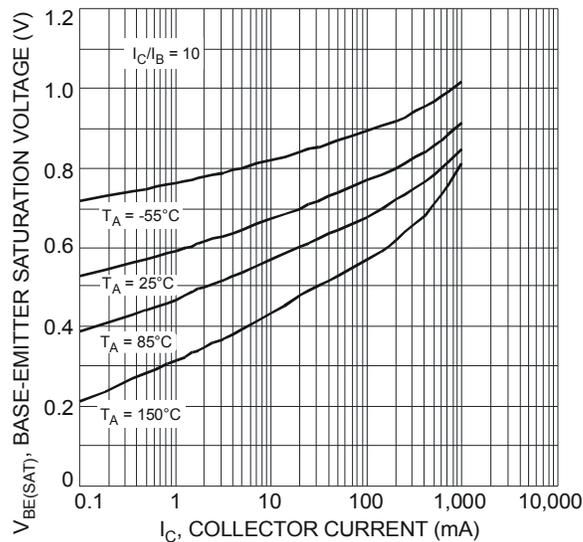


Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current

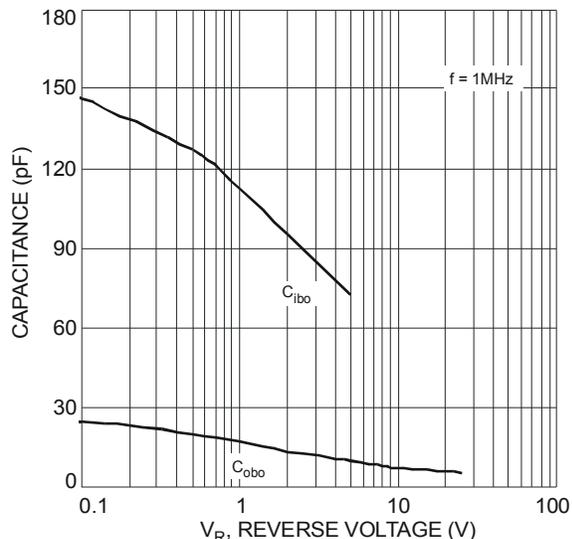
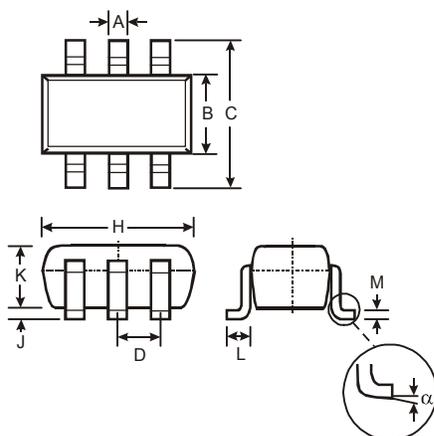


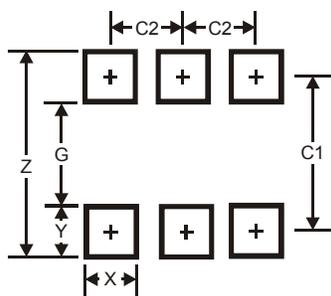
Fig. 9 Typical Capacitance Characteristics

Package Outline Dimensions



SOT26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95